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ABSTRACT OF THE DISCLOSURE

It is an object of the present invention to provide a fine memory cell structure preventing a reaction between 5 an interlayer insulating film and a ferroelectric film and suitable for high integration. According to the invention, there is provided a structure in which a reaction barrier film 43 is interposed between a ferroelectric film 71 and an interlayer insulating film 32 and side walls of a 10 diffusion barrier film 51 are not brought into direct contact with the ferroelectric film 71. Thereby, the reaction between the interlayer insulating film 32 and the ferroelectric film 71 can be restrained and exfoliation of the ferroelectric film 71 can be prevented.

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